MEMORY

Registered

$16 \,\mathrm{M} \times 72 \,\mathrm{BIT}$ SYNCHRONOUS DYNAMIC RAM DIMM

MB8516SR72CA-102/-103/-102L/-103L

168-pin, 4 Clock, 1-bank, based on 16 M × 4 Bit SDRAMs with SPD

DESCRIPTION

The Fujitsu MB8516SR72CA is a fully decoded, CMOS Synchronous Dynamic Random Access Memory (SDRAM) Module consisting of eighteen MB81F64442C devices which organized as four banks of 16 M × 4 bits and a 2K-bit serial EEPROM on a 168-pin glass-epoxy substrate.

The MB8516SR72CA features a fully synchronous operation referenced to a positive edge clock whereby all operations are synchronized at a clock input which enables high performance and simple user interface coexistence.

The MB8516SR72CA is optimized for those applications requiring high speed, high performance and large memory storage, and high density memory organizations.

This module is ideally suited for server system, workstations, high-end PCs, and other applications where enhanced performance is needed.

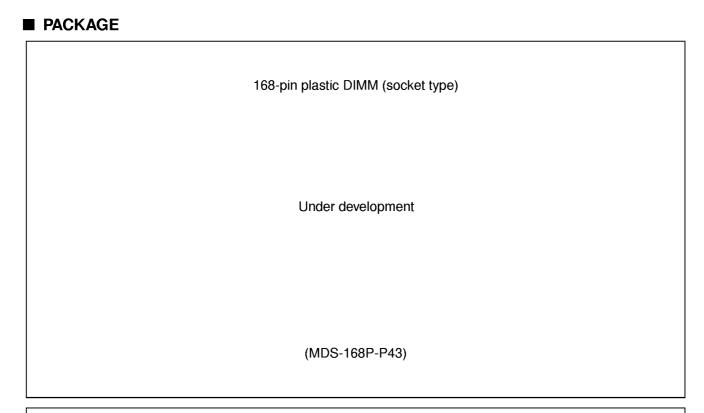
■ PRODUCT LINE & FEATURES

Р	arameter		MB8516SR72CA-102/-102L	MB8516SR72CA-103/-103L		
CL-trcd-trp		. ****	2-2-2 clk min.	3-2-2 clk min.		
Clock Frequency			100 MHz max.	100 MHz max.		
Burst Mode Cycle	Registered CL = 2*		10ns min.	15ns min.		
Time	Mode	CL = 3*	10ns min.	10ns min.		
Output Valid from	Registered	CL = 2*	6 ns	8 ns		
Clock	Mode	CL = 3*	6 ns	6 ns		
	Two Banks Active		13540 mW max.			
Power Dissipation	Self Refresh Mod	e	495 mW max. (Std. power) 455 mW max. (Low power)			
			455 mW max	. (Low power)		

Note *: For registered mode, actual CAS Latency is added one cycle to the CAS Latency of device because of a delay by registers.

- Registered 168-pin DIMM Socket Type (Lead pitch: 1.27 mm)
- Conformed to JEDEC Standard
- Organization: 16,777,216 words × 72 bits
- 3.3 V ±0.3 V Supply Voltage
- All input/output LVTTL compatible
- Conformed to Intel PC/100 spec

- 4096 Refresh Cycle every 65.6 ms
- · Auto and Self Refresh
- CKE Power Down Mode
- DQM Byte Masking (Read/Write)
- Memory: MB81F64442C (16 M× 4, 4-bank) × 18 pcs Serial Presence Detect (SPD) with Serial EEPROM: Intel SPD spec Rev 1.2A Format
 - · Module size:
 - 1.70" (height) \times 5.25" (length) \times 0.32" (thickness)

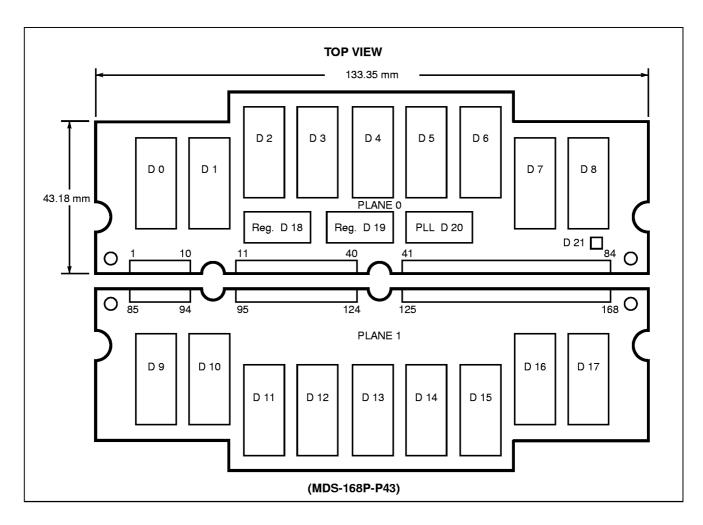


Package and Ordering Information

- 168-pin DIMM, order as MB8516SR72CA-xxxDG (DG = Std. power ver., Gold pad) MB8516SR72CA-xxxLDG (LDG = Low power ver., Gold pad)

■ PIN ASSIGNMENTS

Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name
1	Vss	29	DQMB ₁	57	DQ ₁₈	85	Vss	113	DQMB₅	141	DQ50
2	DQ₀	30	S ₀	58	DQ19	86	DQ32	114	N.C.	142	DQ ₅₁
3	DQ ₁	31	N.C.	59	Vcc	87	DQ ₃₃	115	RAS	143	Vcc
4	DQ ₂	32	Vss	60	DQ20	88	DQ ₃₄	116	Vss	144	DQ52
5	DQ₃	33	A 0	61	N.C.	89	DQ ₃₅	117	A 1	145	N.C.
6	Vcc	34	A 2	62	N.C.	90	Vcc	118	A 3	146	N.C.
7	DQ ₄	35	A 4	63	N.C.	91	DQ36	119	A 5	147	REGE
8	DQ₅	36	A 6	64	Vss	92	DQ ₃₇	120	A ₇	148	Vss
9	DQ ₆	37	A 8	65	DQ ₂₁	93	DQ ₃₈	121	A 9	149	DQ53
10	DQ ₇	38	A 10	66	DQ22	94	DQ39	122	B A o	150	DQ ₅₄
11	DQ ₈	39	BA ₁	67	DQ ₂₃	95	DQ ₄₀	123	A 11	151	DQ55
12	Vss	40	Vcc	68	Vss	96	Vss	124	Vcc	152	Vss
13	DQ₃	41	Vcc	69	DQ ₂₄	97	DQ ₄₁	125	CLK ₁	153	DQ ₅₆
14	DQ ₁₀	42	CLK₀	70	DQ ₂₅	98	DQ ₄₂	126	N.C.	154	DQ ₅₇
15	DQ ₁₁	43	Vss	71	DQ ₂₆	99	DQ ₄₃	127	Vss	155	DQ58
16	DQ ₁₂	44	N.C.	72	DQ ₂₇	100	DQ ₄₄	128	CKE₀	156	DQ59
17	DQ13	45	\overline{S}_2	73	Vcc	101	DQ ₄₅	129	N.C.	157	Vcc
18	Vcc	46	DQMB ₂	74	DQ ₂₈	102	Vcc	130	DQMB6	158	DQ60
19	DQ ₁₄	47	DQMB₃	75	DQ29	103	DQ ₄₆	131	DQMB ₇	159	DQ ₆₁
20	DQ ₁₅	48	N.C.	76	DQ30	104	DQ ₄₇	132	N.C.	160	DQ62
21	CB ₀	49	Vcc	77	DQ ₃₁	105	CB ₄	133	Vcc	161	DQ63
22	CB ₁	50	N.C.	78	Vss	106	CB₅	134	N.C.	162	Vss
23	Vss	51	N.C.	79	CLK ₂	107	Vss	135	N.C.	163	CLK ₃
24	N.C.	52	CB ₂	80	N.C.	108	N.C.	136	CB ₆	164	N.C.
25	N.C.	53	СВз	81	N.C. (WP)	109	N.C.	137	CB ₇	165	SA ₀
26	Vcc	54	Vss	82	SDA	110	Vcc	138	Vss	166	SA ₁
27	WE	55	DQ ₁₆	83	SCL	111	CAS	139	DQ ₄₈	167	SA ₂
28	DQMB₀	56	DQ ₁₇	84	Vcc	112	DQMB ₄	140	DQ49	168	Vcc



■ PIN DESCRIPTIONS

Symbol	I/O	Function	Symbol	I/O	Function
Ao to A ₁₁	I	Address Input	DQo to DQ63	I/O	Data Input/Data Output
BAo, BA ₁	ı	Bank Select (Bank Address)	CBo to CB7	I/O	ECC Data Input/Output
RAS		Row Address Strobe	Vcc	_	Power Supply (+3.3 V)
CAS	I Column Address Strobe		Vss	_	Ground (0 V)
WE		Write Enable	N.C.	_	No Connection
CLK₀ to CLK₃	I	Clock Input	SA ₀ to SA ₂	ı	Serial PD Address Input
CKE₀	I	Clock Enable	SCL	ı	Serial PD Clock
<u>S</u> ₀, <u>S</u> ₂	I	Chip Select	SDA	I/O	Serial PD Address & Data Input/Output
REGE *1	I	Register Enable	WP	ı	Serial PD Write Protect
DQMB ₀ to DQMB ₇	I	Data (DQ) Mask			_

Notes: *1. REGE pin is to switch the module function mode to Registered Mode, or Buffered Mode. For Registered Mode function, REGE = V_{IH} .

■ SERIAL-PD INFORMATION

_	_		Hex \	/alue
Byte	Function Described		-102/- 102L	-103/- 103L
0	Defines Number of Bytes Written into Serial Memory at Module Manufacture	128 Byte	80h	80h
1 1	Total Number of Bytes of SPD Memory Device	256 Byte	08h	08h
2	Fundamental Memory Type	SDRÁM	04h	04h
3	Number of Row Addresses	12	0Ch	0Ch
4	Number of Column Addresses	. 10	0Ah	0Ah
5	Number of Module Banks	1 bank	01h	01h
1 2 3 4 5 6 7 8 9	Data Width	72 bit	48h	48h
	Data Width (Continuation)	+0 LVTTL	00h	00h
6	Interface Type SDRAM Cycle Time (Highest CAS Latency)	10 / 10 ns	01h A0h	01h A0h
10	SDRAM Access from Clock (Highest CAS Latency)	6 / 6 ns	60h	60h
11	DIMM Configuration Type	ECC	02h	02h
12	Refresh Rate/Type	Self, Normal	80h	80h
13	Primary SDRAM Width	×4	04h	04h
14	Error Checking SDRAM Width	×4	04h	04h
15	Minimum Clock Delay for Back to Back Random Column Addresses	1 Cycle	01h	01h
16	Burst Lengths Supported	1, 2, 4, 8, Page	8Fh	8Fh
17	Number of Banks on Each SDRAM Device	4 bank	04h	04h
18	CAS Latency Supported	2,3	06h	06h
19	CS Latency	0	01h	01h
20 21	Write Latency	0 Degistered	01h	01h 1Fh
22	SDRAM Module Attributes SDRAM Device Attributes : General	Registered *1	1Fh 0Eh	0Eh
23	SDRAM Cycle Time (2nd. Highest CAS Latency)	10 / 15 ns	A0h	F0h
24	SDRAM Access from Clock (2nd. Highest CAS Latency)	6 / 8 ns	60h	80h
25	SDRAM Cycle Time (3rd. Highest CAS Latency)	No Support	00h	00h
26	SDRAM Access from Clock (3rd. Highest CAS Latency)	No Support	00h	00h
27	Minimum Row Precharge Time (trp)	20 / 2 ['] 0 ns	14h	14h
28	Row Activate to Row Activate Minimum (tred)	20 / 20 ns	14h	14h
29	RAS to CAS Delay Min. (trcd)	20 / 20 ns	14h	14h
30	Minimum RAS Pulse Width	50 / 50 ns	32h	32h
31	Module Bank Density	128 MByte	20h	20h
31 32 33	Command and Address Signal Input Setup Time	2 ns	20h	20h
33	Command and Address Signal Input Hold Time	1 ns	10h 20h	10h 20h
34 35	Data Signal Input Setup Time Data Signal Input Hold Time	2 ns 1 ns	10h	10h
36 to 61	Unused Storage Locations	1 115	00h	00h
62	SPD Data Revision Code	1.2	12h	12h
63	Checksum for Byte 0 to 62	*2	3Fh	ÁFh
64 to 71	Manufacturer's JEDEC ID Code Per JEP-108E	Optional	00h	00h
72	Manufacturing Location	Optional	00h	00h
	Manufacturer [™] s Part Number	Optional	00h	00h
91 to 92	Revision Code _	Optional	00h	00h
93 to 94	Manufacturing Data	Optional	00h	00h
95 to 98	Assembly Serial Number	Optional	00h	00h
99 to 125		Optional	00h	00h
126 127	Intel Specification Frequency Intel Specification Details for 100 MHz Support	100 MHz CL = 2, 3 / 3	64h	64h
128+	Unused Storage Locations	OL = 2, 3 / 3	8Fh —	8Dh
120+	Unused Giorage Locations			

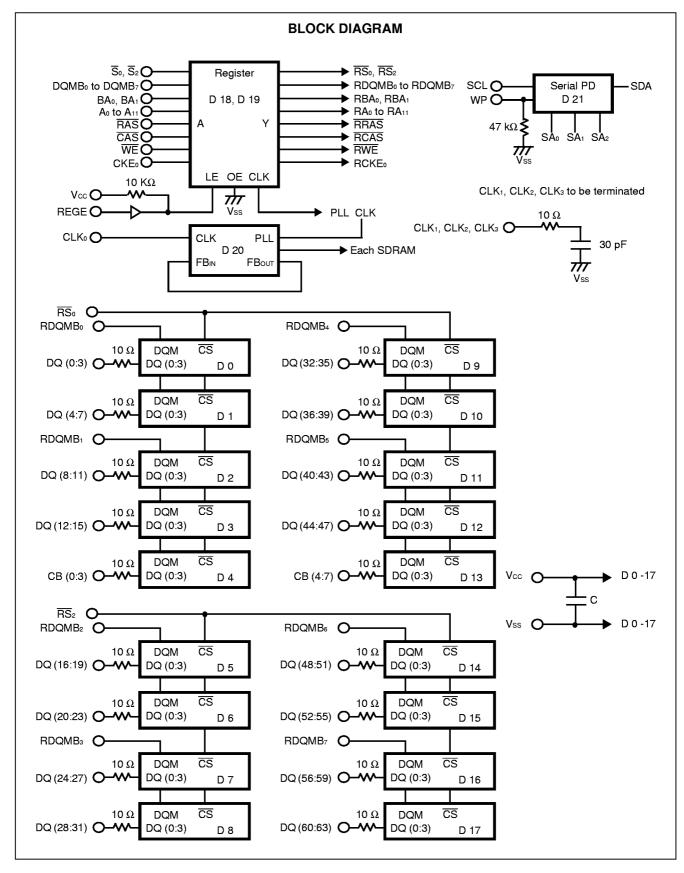
Note: Any write operation must NOT be executed into the addresses of Byte 0 to Byte 127. Some or all data stored into Byte 0 to Byte 127 may be broken.

*1. Byte 22: SDRAM Device Attributes

Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
TBD	TBD	Upper Vcc tolerance	Lower Vcc tolerance	Supports Write 1 /Read Burst	Supports Precharge All	Supports Auto- Precharge	Supports Early RAS Precharge
0	0	0	0	1	1	1	0

^{*2.} Byte 63: Checksum for Byte 0 to 62

This byte is the checksum for Byte 0 through 62. This byte contains the value of the low 8-bits of the arithmetic sum of Byte 0 through 62.



■ ABSOLUTE MAXIMUM RATINGS (See WARNING)

Doromotor	Symbol	Va	lue	l lmit
Parameter	Symbol	Min.	Max.	Unit
Supply Voltage*	Vcc	-0.5	+4.6	V
Input Voltage*	VIN	-0.5	+4.6	V
Output Voltage*	V out	-0.5	+4.6	V
Storage Temperature	Тѕтс	– 55	+125	°C
Power Dissipation	PD	_	21	w
Output Current (D.C.)	Іоит	– 50	+50	mA

^{* :} Voltages referenced to Vss (= 0 V)

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Notes	Symbol		Unit		
Faranielei	Notes	Syllibol	Min.	Тур.	Max.	Oilit
Supply Voltage	*4	Vcc	3.0	3.3	3.6	V
Supply Voltage	I	Vss	0	0	0	V
Input High Voltage, All Inputs	*1, 2	VIH	2.0	_	Vcc +0.5	V
Input Low Voltage, All Inputs	*1, 3	VIL	-0.5	_	0.8	V
Ambient Temperature		TA	0	_	+70	°C

^{*1.} Voltages referenced to Vss (=0V)

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

> Always use semiconductor devices within their recommended operating conditionranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

> No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.

^{*2.} Overshoot limit: V_{H} (max.) = V_{CC} +1.5 V with a pulse-width ≤ 5 ns.

^{*3.} Undershoot limit: V_{\perp} (min.) = -1.5 V with a pulse-width ≤ 5 ns.

■ CAPACITANCE

 $(Vcc = +3.3 \text{ V}, f = 1 \text{ MHz}, T_A = +25^{\circ}C)$

Помото	ha.	Cumbal	Va	lue	Linit
Parame	lei	Symbol	Min.	Max.	Unit
	Ao to A11, BA0, BA1	C _{IN1}	_	8	pF
	RAS, CAS, WE	C _{IN2}	_	9	pF
	$\overline{S}_0, \overline{S}_2$	Сімз	_	10	pF
	CKE₀	C _{IN4}	_	14	pF
Input Capacitance	CLK₀ to CLK₃	C _{IN5}	_	38	pF
	DQMBo to DQMB7	CIN6	-	9	pF
	SCL	C _{IN7}	_	5	pF
	SA ₀ , SA ₁ , SA ₂	C _{IN8}	_	6	pF
	REGE	CIN9	_	23	pF
	SDA	Csda	_	6	pF
Input/Output Capacitance	DQo to DQ63	CDQ	_	13	pF
	CBo to CB7	Ссв	_	13	pF

■ DC CHARACTERISTICS

(At recommended operating conditions unless otherwise noted.) Notes 1, 2, 3

					Value		
Parameter	Notes	Symbol	Condition		Ma	ax.	Unit
		- J	Contained:	Min.	Std. ver.	Low ver.	
Operating Current	*4	Icc1s	Burst Length = 1, t_{RC} = min for BL = 1, t_{CK} = min, One Bank Active, Outputs Open, Address changed up to 1 time during t_{CK} (min.), $0 \ V \le V_{IN} \le V_{IL}$ max V_{IH} min $\le V_{IN} \le V_{CC}$	_	2130		mA
(Average Power Supply Current)	*4 -	Ісств	Burst Length = 1 (each Bank), t_{RC} = min for BL = 1 (each Bank), t_{CK} = min, Two Banks Active, Outputs Open, Address changed up to 1 time during t_{CK} (min.), $0 \text{ V} \leq V_{\text{IN}} \leq V_{\text{IL}}$ max V_{IH} min $\leq V_{\text{IN}} \leq V_{\text{CC}}$	ļ	3760		mA
	*4	ICC2P	$\label{eq:cke} \begin{array}{l} CKE = V_{\text{IL}}, \ t_{\text{CK}} = min, \\ All \ Banks \ Idle, \\ Power \ Down \ Mode, \\ 0 \ V \leq V_{\text{IN}} \leq V_{\text{IL}} \ max \\ V_{\text{IH}} \ min \leq V_{\text{IN}} \leq V_{\text{CC}} \end{array}$	_	155	137	mA
		lcc2PS	$\label{eq:cke} \begin{split} CKE &= V_{\text{IL}},\\ CLK &= V_{\text{IH}} \text{ or } V_{\text{IL}},\\ All \text{ Banks Idle,}\\ \text{Power Down Mode,}\\ 0 V \leq V_{\text{IN}} \leq V_{\text{IL}} \text{ max}\\ V_{\text{IH}} \text{ min } \leq V_{\text{IN}} \leq V_{\text{CC}} \end{split}$	_	137	128	mA
Precharge Standby Current (Power Supply Current)		Icc2N	CKE = VIH, tck = min, All Banks Idle, NOP commands only, Input signals (except to CMD) are changed one time during 3 clock cycles, 0 V \leq VIN \leq VIL max VIH min \leq VIN \leq VCC	— 390		mA	
		Icczns	$\begin{array}{l} CKE = V_{\text{IH}}, \\ CLK = V_{\text{IH}} \text{ or } V_{\text{IL}}, \\ All \text{ Banks Idle,} \\ Input \text{ Signals are Stable,} \\ 0 V \leq V_{\text{IN}} \leq V_{\text{IL}} \text{ max} \\ V_{\text{IH}} \text{ min} \leq V_{\text{IN}} \leq V_{\text{CC}} \end{array}$	_	— 155		mA

(Continued)

(Continued)

				Value		
Parameter Notes	Symbol	Condition		Ma	ax.	Unit
			Min.	Std. ver.	Low ver.	
	Іссзр	$\label{eq:cke} \begin{array}{l} CKE = V_{\text{IL}}, t_{\text{CK}} = min, \\ \text{Any Bank Active}, \\ 0 V \leq V_{\text{IN}} \leq V_{\text{IL}} \text{max} \\ V_{\text{IH}} min \leq V_{\text{IN}} \leq V_{\text{CC}} \end{array}$	_	155	137	mA
	Іссзрѕ	$\label{eq:cke} \begin{array}{l} CKE = V_{\text{IL}}, \\ CLK = V_{\text{IH}} \text{ or } V_{\text{IL}}, \\ Any \text{ Bank Active}, \\ 0 V \leq V_{\text{IN}} \leq V_{\text{IL}} \text{ max} \\ V_{\text{IH}} \text{ min } \leq V_{\text{IN}} \leq V_{\text{CC}} \end{array}$	_	137	128	mA
Active Standby Current *4 (Power Supply Current)	Іссзи	CKE = V_{IH} , t_{CK} = min, Any Bank Active, NOP commands only, Input signals (except to CMD) are changed one time during 3 clock cycles, $0 \text{ V} \leq V_{\text{IN}} \leq V_{\text{IL}}$ max V_{IH} min $\leq V_{\text{IN}} \leq V_{\text{CC}}$	_	5	70	mA
	Іссэня	$\begin{array}{l} CKE = V_{IH}, \\ CLK = V_{IH} \ or \ V_{IL}, \\ Any \ Bank \ Active, \\ 0 \ V \leq V_{IN} \leq V_{IL} \ max \\ V_{IH} \ min \leq V_{IN} \leq V_{CC} \end{array}$	_	155		mA
Burst Mode Current (Average Power Supply Current) *4	Icc4	tck = min, Gapless data, Burst Length = 4, Outputs open, Multiple-banks Active, $0 \ V \le V_{\text{IN}} \le V_{\text{IL}} \max$ $V_{\text{IH}} \min \le V_{\text{IN}} \le V_{\text{CC}}$	_	— 1835		mA
Auto-refresh Current *4 (Average Power Supply Current)	Іссь	Auto Refresh, $t_{\text{CK}} = \text{min}, \\ t_{\text{RC}} = \text{min}, \\ 0 \ V \leq V_{\text{IN}} \leq V_{\text{IL}} \text{max} \\ V_{\text{IH}} \ \text{min} \leq V_{\text{IN}} \leq V_{\text{CC}}$	_	44	-56	mA
Self-refresh Current *4 (Average Power Supply Current)	Icc ₆	$\label{eq:Self-refresh} \begin{array}{l} \text{Self-refresh, } t_{\text{CK}} = \text{min,} \\ \text{CKE} \leq 0.2 \text{ V,} \\ 0 \text{ V} \leq \text{V}_{\text{IN}} \leq \text{V}_{\text{IL}} \text{max} \\ \text{V}_{\text{IH}} \text{ min} \leq \text{V}_{\text{IN}} \leq \text{V}_{\text{CC}} \end{array}$	_	137	128	mA
REGE		0 V ≤ V _{IN} ≤ V _{CC}	-50	5	0	^
Input Leakage Current Others	· Iu	All other pins not under test = 0 V	-10	10		μΑ
Output Leakage Current	Ісо	Output is disabled (Hi-Z) 0 V ≤ V _{IN} ≤ V _{CC}	-10	10		μА
LVTTL Output High Voltage *5	Vон	Iон = −2.0 mA	2.4 —		_	V
LVTTL Output Low Voltage *5	Vol	IoL = +2.0 mA	_	0	.4	V

Notes: *1. An initial pause (DESL on NOP) of 200 μs is required after power-on followed by a minimum of eight Auto-refresh cycles.

- *2. Values of lcc1s, lcc1D and lcc4 are for when one side of the double-sided module is in standby mode (lcc2N) and the other side is in active.
- *3. DC characteristics is the Serial PD standby state ($V_{IN} = GND$ or V_{CC}).
- *4. lcc depends on the output termination, load conditions, clock cycle rate and signal clock rate. The specified values are obtained with the output open and no termination resistors.
- *5. Voltages referenced to Vss (= 0 V)

■ AC CHARACTERISTICS

(SDRAM Component Specifications) Notes 1, 2, 3

(1) BASE CHARACTERISTICS

(At recommended operating conditions unless otherwise noted.)

No.	Parameter	Not	Notes		400/	SR72CA -102L	MB8516 -103/-	SR72CA -103L	Unit
					Min.	Max.	Min.	Max.	
1	Clock Period	*4	CL = 2	t ck2	10		15		ns
'	T Glock Ferrida	4	CL = 3	t ck3	10	_	10	_	115
2	Clock High Time		tсн	3	_	3	_	ns	
3	Clock Low Time	t cL	3	_	3	_	ns		
4	Input Setup Time	Registere	t sı	3.5	_	3.5	_	ns	
5	Input Hold Time	Registere	d Mode	tнı	2.5	_	2.5	_	ns
6	Output Valid from Clock	*4, *5, *6	CL = 2	t _{AC2}	_	6		8	
0	(tck = min)		CL = 3	t AC3	_	6	_	6	ns
7	Output in Low-Z			t ız	0	_	0	_	ns
8	Output in High 7	*4, *7	CL = 2	t _{HZ2}	3	6	3	8	100
0	Output in High-Z	4, 7	CL = 3	tнzз	3	6	3	6	ns
9	Output Hold Time			tон	3	_	3	_	ns
10	Time between Refresh			tref	<u>—</u>	65.6	_	65.6	ms
11	Transition Time			t⊤	0.5	2	0.5	2	ns
12	CKE Setup Time for Power Down Exit Time	Registere	d Mode	t cksp	3.5	_	3.5	_	ns

(2) BASE VALUES FOR CLOCK COUNT/LATENCY

No.	Parameter	No	tes	Symbol	MB85169 -102/-103/-	Unit		
				_	Min.	Max.		
1	RAS Cycle Time		*8	t rc	70		ns	
2	RAS Precharge Time			t RP	20	_	ns	
3	RAS Active Time			tras	50	110000	ns	
4	RAS to CAS Delay Time		*9	trcd	20		ns	
5	Write Recovery Time			twr	10	_	ns	
6	Data-in to Precharge Lead Time			t dpl	10		ns	
7	Data-in to Active/Refresh Command Period	*4	CL = 2	tdal2	1 cyc + trp		nc	
′	Data-III to Active/Hellesh Command Fellod	4	CL = 3	t _{DAL3}	2 cyc + trp	_	ns	
8	Mode Register Set Cycle Time			trsc	20		ns	
9	RAS to RAS Bank Active Delay Time			t rrd	20	_	ns	

(3) CLOCK COUNT FORMULA (*10)

$$Clock \ge \frac{Base\ Value}{Clock\ Period}\ \ (Round\ off\ a\ whole\ number)$$

(4) LATENCY (The latency values on these parameters are fixed regardless of clock period.)

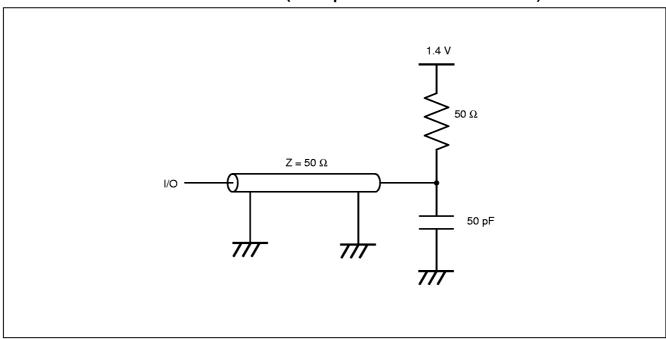
No.	Parameter	1	Notes	Symbol	MB8516SR72CA -102/-103/-102L/-103L Registered Mode	Unit
1	CKE to Clock Disable			Icke	2	Cycle
2	DQM to Output in High-Z			lpqz	3	Cycle
3	DQM to Input Data Delay			IDQD	1	Cycle
4	Last Output to Write Command Delay			lowd	1	Cycle
5	Write Command to Input Data Delay			I _{DWD}	1	Cycle
	Drachards to Output in High 7 Delev	*4	CL = 2	Ігон2	3	Cyclo
6	Precharge to Output in High-Z Delay	4	CL = 3	Ігонз	4	Cycle
7	Burst Stop Command to Output in High-Z Delay	*4	CL = 2	I _{BSH2}	3	Cycle
			CL = 3	Івѕнз	4	
8	CAS to CAS Delay (min)			Iccd	1	Cycle
9	CAS Bank Delay (min)			Ісво	1	Cycle

- Notes: *1. An initial pause (DESL on NOP) of 200 μs is required after power-up followed by a minimum of eight Auto-refresh cycles.
 - *2. 1.4 V or V_{REF} is the reference level for measuring timing of signals. Transition times are measured between V_{IH} (min) and V_{IL} (max).
 - *3. AC characteristics assume $t_T = 1$ ns and 50 pF of capacitance load.
 - *4. For Registered Mode, actual CAS Latency is added one cycle to the CAS Latency of this value because of a delay by registers.
 - *5. Assumes trop is satisfied.
 - *6. tac also specifies the access time at burst mode except for first access.
 - *7. Specified where output buffer is no longer driven.
 - *8. Actual clock count of the (Inc) will be sum of clock count of that (Inas) and the (Inp).
 - *9. Operation within the tred (min) ensures that access time is determined by tred (min) +tac (max); if tred is greater than the specified tred (min), access time is determined by tred.
 - *10. All base values are measured from the clock edge at the command input to the clock edge for the next command input.

All clock counts are calculated by a simple formula:

clock count equals base value divided by clock period (round off to a whole number).

■ AC OPERATING TEST CONDITION (Example of AC Test Load Circuit)



^{*}Source: See MB81F64442C Data Sheet for details on the electrical.

■ SERIAL PRESENCE DETECT(SPD) FUNCTION

1. PIN DESCRIPTIONS

SCL (Serial Clock)

SCL input is used to clock all data input/output of SPD.

SDA (Serial Data)

SDA is a common pin used for all data input/output of SPD. The SDA pull-up resistor is required due to the open-drain output.

SA₀, SA₁, SA₂ (Address)

Address inputs are used to set the least significant three bits of the eight bits slave address. The address inputs must be fixed to select a particular module and the fixed address of each module must be different each other.

2. SPD OPERATIONS

CLOCK and DATA CONVENTION

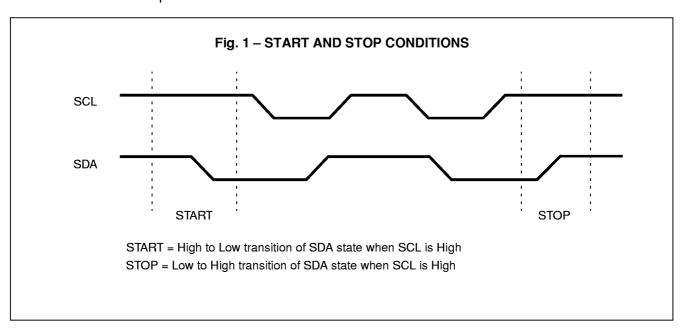
Data states on the SDA can change only during SCL= Low. SDA state changes during SCL = High are indicated start and stop conditions. Refer to Fig. 1 below.

START CONDITION

All commands are preceded by a start condition, which is a transition of SDA state from High to Low when SCL = High. SPD will not respond to any command until this condition has been met.

STOP CONDITION

All read or write operation must be terminated by a stop condition, which is a transition of SDA state from Low to High when SCL = High. The stop condition is also used to make the SPD into the state of standby power mode after a read sequence.



ACKNOWLEDGE

Acknowledge is a software convention used to indicate successful data transfer. The transmitting device, either master or slave, will release the bus after transmitting eight bits. During the ninth clock cycle the receiver will put the SDA line to Low in order to acknowledge that it received the eight bits of data.

The SPD will respond with an acknowledge when it received the start condition followed by slave address issued by master.

In the read operation, the SPD will transmit eight bits of data, release the SDA line and monitor the line for an acknowledge. If an acknowledge is detected and no stop condition is issued by master, the SPD will continue to transmit data. If an acknowledge is not detected, the SPD will terminated further data transmissions. The master must then issue a stop condition to return the SPD to the standby power mode.

In the write operation, upon receipt of eight bits of data the SPD will respond with an acknowledge, and await the next eight bits of data, again responding with an acknowledge until the stop condition is issued by master.

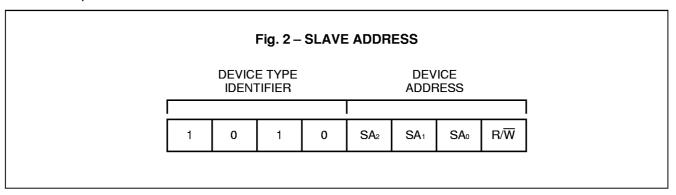
SLAVE ADDRESS ADDRESSING

Following a start condition, the master must output the eight bits slave address. The most significant four bits of the slave address are device type identifier. For the SPD this is fixed as 1010[B]. Refer to the Fig. 2 below.

The next three significant bits are used to select a particular device. A system could have up to eight SPD devices —namely up to eight modules— on the bus. The eight addresses for eight SPD devices are defined by the state of the SA₀, SA₁ and SA₂ inputs.

The last bit of the slave address defines the operation to be performed. When R/\overline{W} bit is "1", a read operation is selected, when R/\overline{W} bit is "0", a write operation is selected.

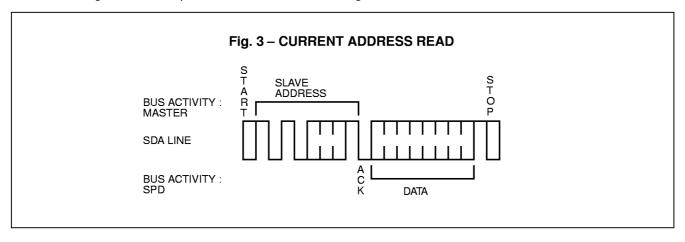
Following the start condition, the SPD monitors the SDA line comparing the slave address being transmitted with its slave address (device type and state of SA_0 , SA_1 , and SA_2 inputs). Upon a correct compare the SPD outputs an acknowledge on the SDA line. Depending on the state of the R/\overline{W} bit, the SPD will execute a read or write operation.



3. READ OPERATIONS

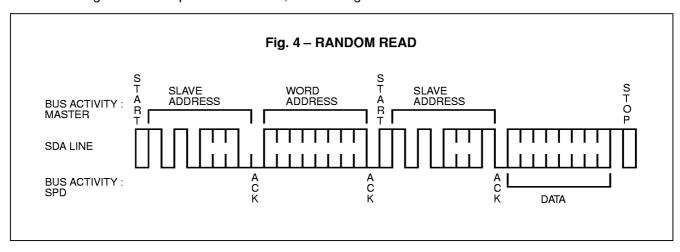
CURRENT ADDRESS READ

Internally the SPD contains an address counter that maintains the address of the last data accessed, incriminated by one. Therefore, if the last access (either a read or write operation) was to address(n), the next read operation would access data from address(n+1). Upon receipt of the slave address with the R/W bit = "1", the SPD issues an acknowledge and transmits the eight bits of data during the next eight clock cycles. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig. 3 for the sequence of address, acknowledge and data transfer.



RANDOM READ

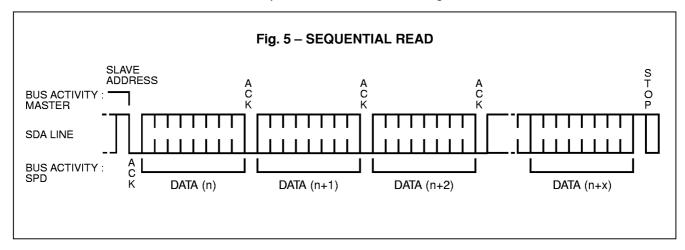
Random Read operations allow the master to access any memory location in a random manner. Prior to issuing the slave address with the R/\overline{W} bit = "1", the master must first perform a "dummy" write operation on the SPD. The master issues the start condition, and the slave address followed by the word address. After the word address acknowledge, the master immediately reissues the start condition and the slave address with the R/\overline{W} bit = "1". This will be followed by an acknowledge from the SPD and then by the eight bits of data. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig. 4 for the sequence of address, acknowledge and data transfer.



SEQUENTIAL READ

Sequential Read can be initiated as either a current address read or random read. The first data are transmitted as with the other read mode, however, the master now responds with an acknowledge, indicating it requires additional data. The SPD continues to output data for each acknowledge received. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig. 5 for the sequence of address, acknowledge and data transfer.

The data output is sequential, with the data from address(n) followed by the data from address(n+1). The address counter for read operations increments all address bits, allowing the entire memory contents to be serially read during one operation. At the end of the address space (address 255), the counter "rolls over" to address 0 and the SPD continues to output data for each acknowledge received.



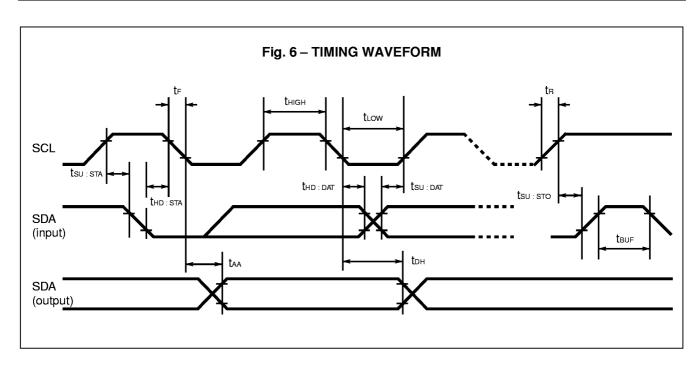
4. DC CHARACTERISTICS

Parameter	Note	Symbol	Condition	Value		Unit
Farameter	Note		Condition	Min.	Max.	Uill
Input Leakage Current		SILI	0 V ≤ V _{IN} ≤ V _{CC}	- 10	10	μΑ
Output Leakage Current		SILO	0 V ≤ Vout ≤ Vcc	–10	10	μΑ
Output Low Voltage	*1	Svol	loL = 3.0 mA		0.4	V

Note: *1. Referenced to Vss.

5. AC CHARACTERISTICS

N.	Parameter	Symbol	Va	I I i A	
No.			Min.	Max.	Unit
1	SCL Clock Frequency	fsc∟	_	100	KHz
2	Noise Suppression Time Constant at SCL, SDA Inputs	Tı	_	100	ns
3	SCL Low to SDA Data Out Valid	taa	_	3.5	μs
4	Time the Bus Must Be Free Before a New Transmission Can Start	t BUF	4.7	_	μs
5	Start Condition Hold Time	thd:STA	4.0		μs
6	Clock Low Period	tLOW	4.7	_	μs
7	Clock High Period	tнідн	4.0	_	μs
8	Start Condition Setup Time	tsu:sta	4.7		μs
9	Data in Hold Time	thd:dat	0	_	μs
10	Data in Setup Time	tsu:dat	250	_	ns
11	SDA and SCL Rise Time	tr	_	1	μs
12	SDA and SCL Fall Time	t⊧	_	300	ns
13	Stop Condition Setup Time	tsu:sto	4.7	_	μs
14	Data Out Hold Time	t DH	100	_	ns
15	Write Cycle Time	twr	_	15	ms



■ PACKAGE DIMENSIONS

168-pin plastic DIMM (socket type) (MDS-168P-P43)		
	Under development	
		Dimension in mm (inches)